

## isc P-Channel MOSFET Transistor

# SPD15P10PG

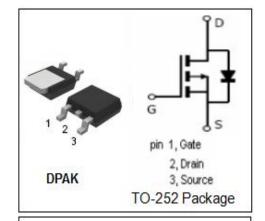
#### ·FEATURES

- Static drain-source on-resistance:
   R<sub>DS</sub>(on)≤240mΩ(@V<sub>GS</sub>= -10V; I<sub>D</sub>= -10.6A)
- Advanced trench process technology
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### APPLICATIONS

• Fast switching application.





| <ul> <li>ABSOLUTE</li> </ul> | MAXIMUM | RATINGS(T | a=25°C |
|------------------------------|---------|-----------|--------|
|------------------------------|---------|-----------|--------|

| SYMBOL           | PARAMETER                               | VALUE   | UNIT          |
|------------------|-----------------------------------------|---------|---------------|
| $V_{DSS}$        | Drain-Source Voltage                    | -100    | V             |
| V <sub>G</sub> s | Gate-Source Voltage                     | ±20     | V             |
| I <sub>D</sub>   | Drain Current-Continuous                | -15     | А             |
| P <sub>D</sub>   | Total Dissipation @T <sub>C</sub> =25°C | 128     | W             |
| Tj               | Max. Operating Junction Temperature     | -55~175 | ${\mathbb C}$ |
| T <sub>stg</sub> | Storage Temperature                     | -55~175 | $^{\circ}$ C  |

## • THERMAL CHARACTERISTICS

| SYMBOL   | PARAMETER                          | MAX  | UNIT |
|----------|------------------------------------|------|------|
| Rth(j-c) | Channel-to-case thermal resistance | 1.17 | °C/W |

|       | A<br>B                | 7           | <u>C 0.5</u> | K T              |
|-------|-----------------------|-------------|--------------|------------------|
| D     | T.                    |             |              |                  |
| 1 1 F | <b>  </b>  <br>   8.0 | 2   3<br>F  |              | 1.50<br>3.0<br>K |
| G H   |                       | Н           |              | L                |
|       |                       | m           | m            |                  |
|       | DIM                   | MIN         | MAX          |                  |
|       | Α                     | 6.40        | 6.60         |                  |
|       | В                     | 5. 20       | 5. 40        | 3                |
|       | D                     | 1. 15       | 1.35         |                  |
|       | F                     | 5. 70<br>0. | 6. 10        | į.               |
|       | G                     | 0.          | 75           | 8                |
|       | Н                     | 2.10        | 2. 50        | 16               |
|       | J                     | 2. 10       | 2.40         |                  |
|       | K                     | 0.40        | 0.60         |                  |
|       | L                     | 0.90        | 1. 10        | é.               |
|       | Q                     | 9.90        | 10.1         | ē                |



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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

| SYMBOL              | PARAMETER                      | CONDITIONS                                                  | MIN  | MAX   | UNIT      |
|---------------------|--------------------------------|-------------------------------------------------------------|------|-------|-----------|
| BV <sub>DSS</sub>   | Drain-Source Breakdown Voltage | V <sub>GS</sub> =0V; I <sub>D</sub> = -1mA                  | -100 |       | V         |
| V <sub>GS(th)</sub> | Gate Threshold Voltage         | V <sub>DS</sub> =V <sub>GS</sub> ; I <sub>D</sub> = -1.54mA | -2.1 | -4    | V         |
| R <sub>DS(on)</sub> | Drain-Source On-Resistance     | V <sub>GS</sub> = -10V; I <sub>D</sub> = -10.6A             |      | 240   | $m\Omega$ |
| Igss                | Gate-Source Leakage Current    | V <sub>GS</sub> = ±20V; V <sub>DS</sub> = 0V                |      | ±100  | nA        |
| I <sub>DSS</sub>    | Drain-Source Leakage Current   | V <sub>DS</sub> = -100V; V <sub>GS</sub> = 0V               |      | -1    | μА        |
| $V_{SD}$            | Diode forward voltage          | I <sub>S</sub> = -15A, V <sub>GS</sub> = 0V                 |      | -1.35 | V         |



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